

74HC4060-Q100; 74HCT4060-Q100

14-stage binary ripple counter with oscillator

Rev. 1 — 2 August 2012

Product data sheet

1. General description

The 74HC4060-Q100; 74HCT4060-Q100 are high-speed Si-gate CMOS devices that comply with JEDEC standard no. 7A. They are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC4060-Q100; 74HCT4060-Q100 are 14-stage ripple-carry counter/dividers and oscillators with three oscillator terminals (RS, RTC and CTC), ten buffered outputs (Q3 to Q9 and Q11 to Q13) and an overriding asynchronous master reset (MR). The oscillator configuration allows design of either RC or crystal oscillator circuits. The oscillator may be replaced by an external clock signal at input RS. In this case keep the other oscillator pins (RTC and CTC) floating. The counter advances on the negative-going transition of RS. A HIGH level on MR resets the counter (Q3 to Q9 and Q11 to Q13 = LOW), independent of other input conditions. In the HCT version, the MR input is TTL compatible, but the RS input has CMOS input switching levels and can be driven by a TTL output by using a pull-up resistor to V_{CC} .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40°C to $+85^{\circ}\text{C}$ and from -40°C to $+125^{\circ}\text{C}$
- All active components on chip
- RC or crystal oscillator configuration
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\ \Omega$)
- Multiple package options

3. Applications

- Control counters
- Timers
- Frequency dividers
- Time-delay circuits



4. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74HC4060D-Q100	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT4060D-Q100				
74HC4060PW-Q100	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HC4060BQ-Q100	−40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal-enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1
74HCT4060BQ-Q100				

5. Functional diagram

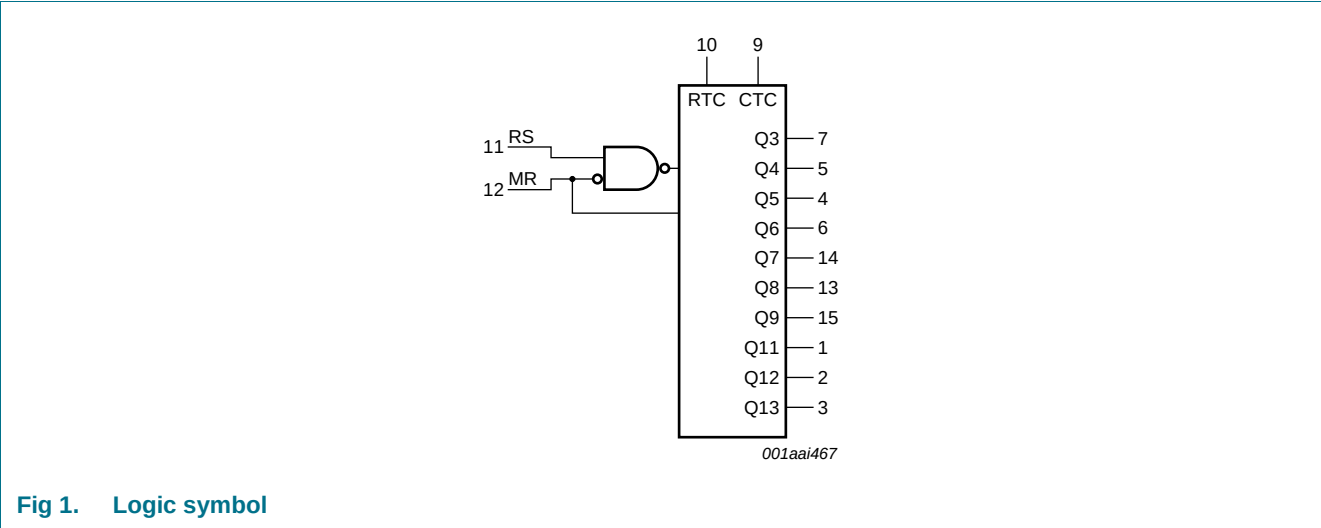


Fig 1. Logic symbol

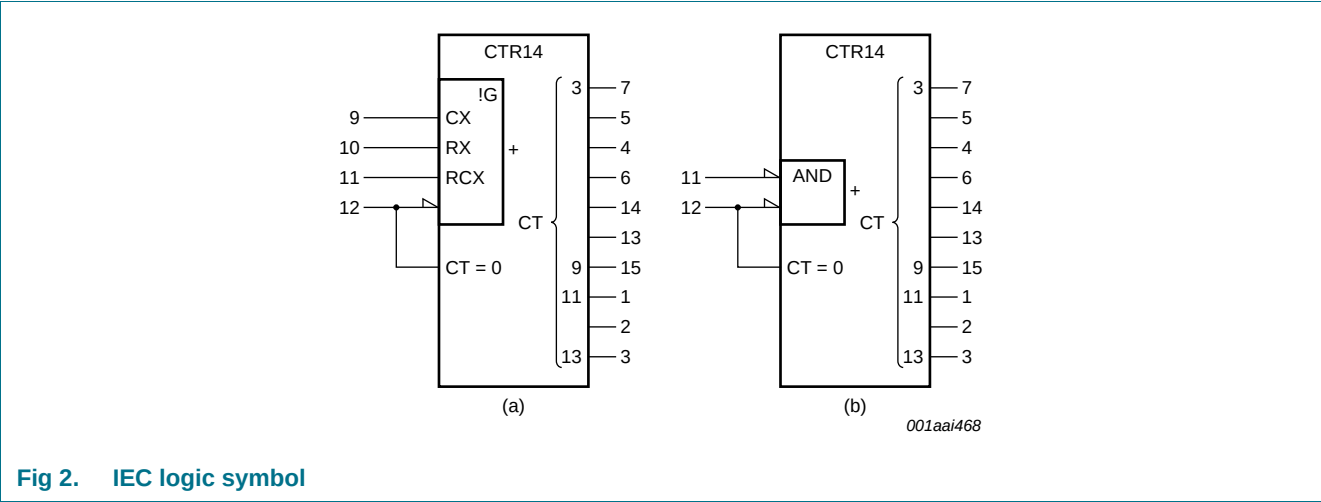


Fig 2. IEC logic symbol

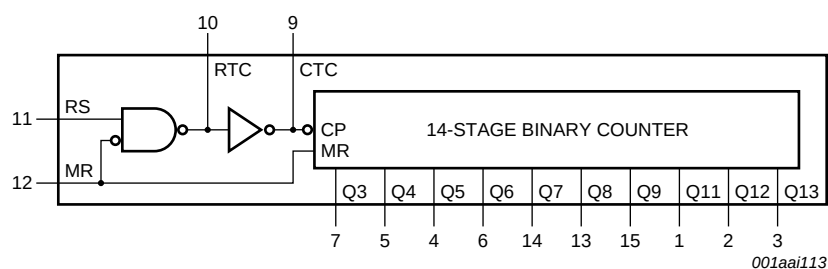


Fig 3. Functional diagram

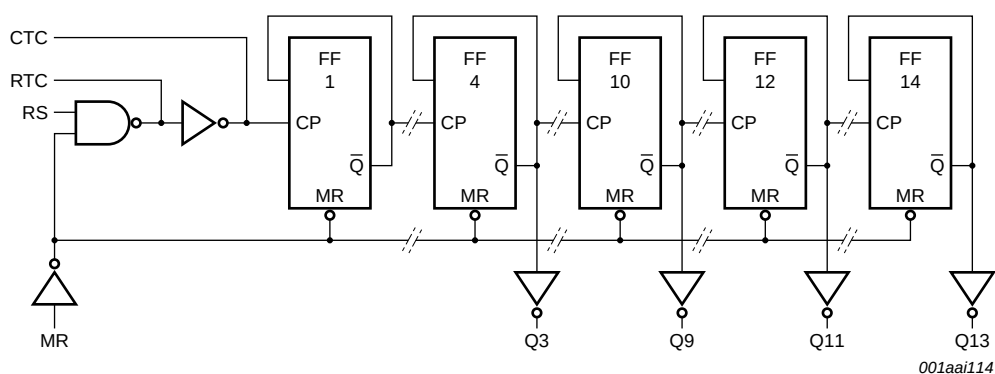
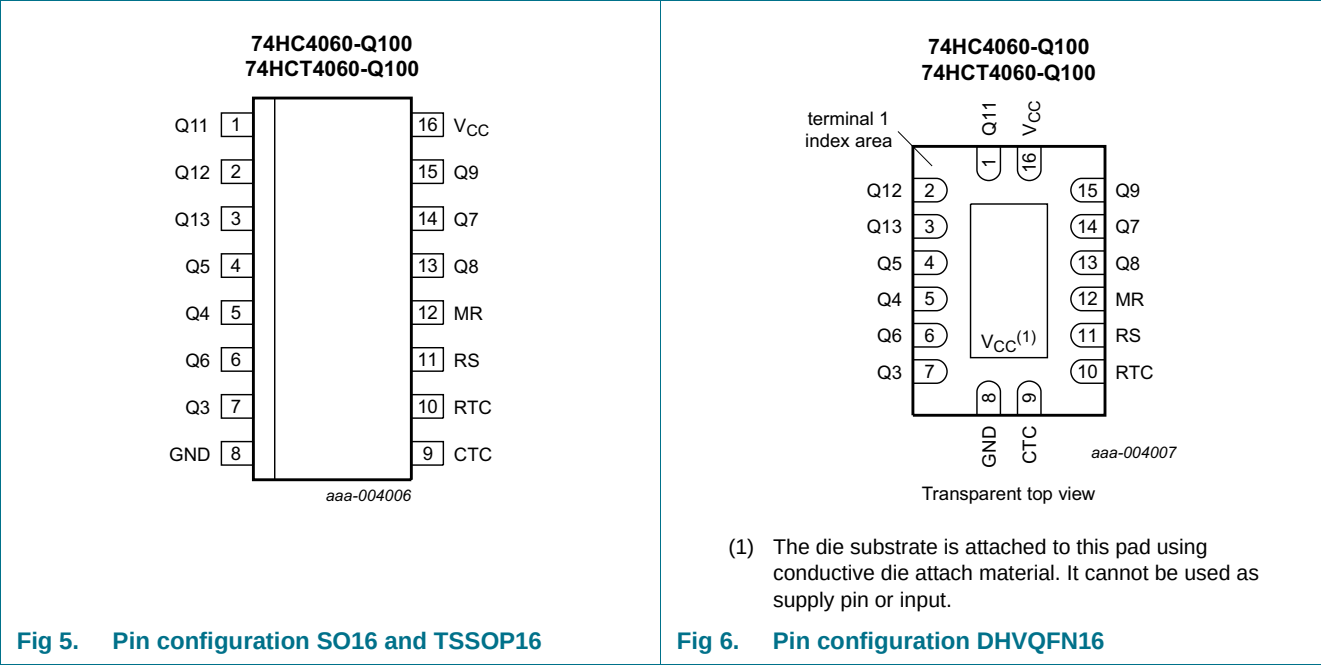


Fig 4. Logic diagram

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
Q11 to Q13	1, 2, 3	counter output
Q3 to Q9	7, 5, 4, 6, 14, 13, 15	counter output
GND	8	ground (0 V)
CTC	9	external capacitor connection
RTC	10	external resistor connection
RS	11	clock input /oscillator pin
MR	12	master reset input (active HIGH)
V _{CC}	16	supply voltage

7. Functional description

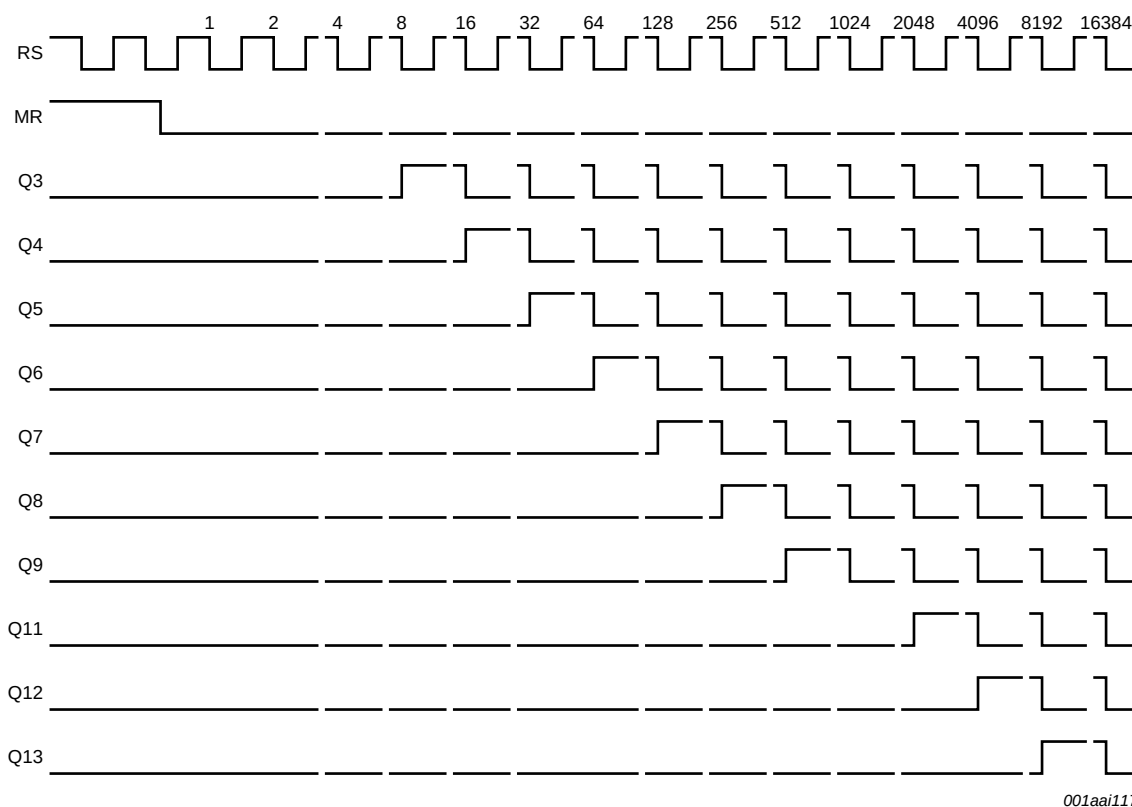


Fig 7. Timing diagram

8. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5 \text{ V}$ or $V_I > V_{CC} + 0.5 \text{ V}$	1 -	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5 \text{ V}$ or $V_O > V_{CC} + 0.5 \text{ V}$	1 -	± 20	mA
I_O	output current	$-0.5 \text{ V} < V_O < V_{CC} + 0.5 \text{ V}$	-	± 25	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C

Table 3. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C			
		SO16 package	[2] -	500	mW
		TSSOP16 package	[3] -	500	mW
		DHVQFN16 package	[4] -	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 8 mW/K above 70 °C.[3] P_{tot} derates linearly with 5.5 mW/K above 60 °C.[4] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

9. Recommended operating conditions

Table 4. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC4060-Q100			74HCT4060-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 5. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC4060-Q100										
V _{IH}	HIGH-level input voltage	MR input								
		V _{CC} = 2.0 V	1.5	1.3	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.1	-	4.2	-	4.2	-	V
		RS input								
		V _{CC} = 2.0 V	1.7	-	-	1.7	-	1.7	-	V
		V _{CC} = 4.5 V	3.6	-	-	3.6	-	3.6	-	V
		V _{CC} = 6.0 V	4.8	-	-	4.8	-	4.8	-	V

Table 5. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V _{IL}	LOW-level input voltage	MR input								
		V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
		RS input								
		V _{CC} = 2.0 V	-	-	0.3	-	0.3	-	0.3	V
		V _{CC} = 4.5 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 6.0 V	-	-	1.2	-	1.2	-	1.2	V
V _{OH}	HIGH-level output voltage	RTC output; RS = MR = GND								
		I _O = –20 µA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = –20 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –20 µA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = –2.6 mA; V _{CC} = 4.5 V	3.98	-	-	3.84	-	3.7	-	V
		I _O = –3.3 mA; V _{CC} = 6.0 V	5.48	-	-	5.34	-	5.2	-	V
		RTC output; RS = MR = V _{CC}								
		I _O = –20 µA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = –20 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –20 µA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = –0.65 mA; V _{CC} = 4.5 V	3.98	-	-	3.84	-	3.7	-	V
		I _O = –0.85 mA; V _{CC} = 6.0 V	5.48	-	-	5.34	-	5.2	-	V
		CTC output; RS = V _{IH} ; MR = V _{IL}								
		I _O = –3.2 mA; V _{CC} = 4.5 V	3.98	-	-	3.84	-	3.7	-	V
		I _O = –4.2 mA; V _{CC} = 6.0 V	5.48	-	-	5.34	-	5.2	-	V
		V _I = V _{IH} or V _{IL} ; except RTC output								
		I _O = –20 µA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = –20 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –20 µA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		V _I = V _{IH} or V _{IL} ; except RTC and CTC outputs								
		I _O = –4.0 mA; V _{CC} = 4.5 V	3.98	-	-	3.84	-	3.7	-	V
		I _O = –5.2 mA; V _{CC} = 6.0 V	5.48	-	-	5.34	-	5.2	-	V

Table 5. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V _{OL}	LOW-level output voltage	RTC output; RS = V _{CC} ; MR = GND								
		I _O = 20 µA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 µA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 2.6 mA; V _{CC} = 4.5 V	-	-	0.26	-	0.33	-	0.4	V
		I _O = 3.3 mA; V _{CC} = 6.0 V	-	-	0.26	-	0.33	-	0.4	V
		CTC output; RS = V _{IL} ; MR = V _{IH}								
		I _O = 3.2 mA; V _{CC} = 4.5 V	-	-	0.26	-	0.33	-	0.4	V
		I _O = 4.2 mA; V _{CC} = 6.0 V	-	-	0.26	-	0.33	-	0.4	V
		V _I = V _{IH} or V _{IL} ; except RTC output								
		I _O = 20 µA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 µA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		V _I = V _{IH} or V _{IL} ; except RTC and CTC outputs								
I _I	input leakage current	I _O = 4.0 mA; V _{CC} = 4.5 V	-	-	0.26	-	0.33	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	-	0.26	-	0.33	-	0.4	V
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	µA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT4060-Q100										
V _{IH}	HIGH-level input voltage	MR input; V _{CC} = 4.5 V to 5.5 V	[1]	2.0	-	-	2.0	-	2.0	V
V _{IL}	LOW-level input voltage	MR input; V _{CC} = 4.5 V to 5.5 V	[1]	-	-	0.8	-	0.8	-	0.8 V

Table 5. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V _{OH}	HIGH-level output voltage	RTC output; RS = MR = V _{CC}								
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -0.65 mA; V _{CC} = 4.5 V	3.98	-	-	3.84	-	3.7	-	V
		RTC output; RS = MR = GND								
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -2.6 mA; V _{CC} = 4.5 V	3.98	-	-	3.84	-	3.7	-	V
		CTC output; RS = V _{IH} ; MR = V _{IL}								
		I _O = -3.2 mA; V _{CC} = 4.5 V	3.98	-	-	3.84	-	3.7	-	V
		V _I = V _{IH} or V _{IL} ; except RTC output								
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		V _I = V _{IH} or V _{IL} ; except RTC and CTC outputs								
		I _O = -4.0 mA; V _{CC} = 4.5 V	3.98	-	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	RTC output; RS = V _{CC} ; MR = GND								
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 2.6 mA; V _{CC} = 4.5 V	-	-	0.26	-	0.33	-	0.4	V
		CTC output; RS = V _{IL} ; MR = V _{IH}								
		I _O = 3.2 mA; V _{CC} = 4.5 V	-	-	0.26	-	0.33	-	0.4	V
		V _I = V _{IH} or V _{IL} ; except RTC output								
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		V _I = V _{IH} or V _{IL} ; except RTC and CTC outputs								
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	-	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; V _{CC} = 5.5 V; I _O = 0 A	-	-	8.0	-	80	-	160	µA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} - 2.1 V; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V; I _O = 0 A	-	40	144	-	180	-	196	µA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

[1] For HCT4060-Q100, only input MR (pin 12) has TTL input switching levels.

11. Dynamic characteristics

Table 6. Dynamic characteristics

$GND = 0\text{ V}$; $C_L = 50\text{ pF}$ unless otherwise specified; for test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC4060-Q100										
t _{pd}	propagation delay	RS to Q3; see Figure 8	[1]							
		V _{CC} = 2.0 V	-	99	300	-	375	-	450	ns
		V _{CC} = 4.5 V	-	36	60	-	75	-	90	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	31	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	29	51	-	64	-	77	ns
		Qn to Qn+1; see Figure 9	[2]							
		V _{CC} = 2.0 V	-	22	80	-	100	-	120	ns
		V _{CC} = 4.5 V	-	8	16	-	20	-	24	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	6	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	6	14	-	17	-	20	ns
t _{PHL}	HIGH to LOW propagation delay	MR to Qn; see Figure 10								
		V _{CC} = 2.0 V	-	55	175	-	220	-	265	ns
		V _{CC} = 4.5 V	-	20	35	-	44	-	53	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	17	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	16	30	-	37	-	45	ns
t _t	transition time	Qn; see Figure 8	[3]							
		V _{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V _{CC} = 6.0 V	-	6	13	-	16	-	19	ns
t _w	pulse width	RS (HIGH or LOW); see Figure 8								
		V _{CC} = 2.0 V	80	17	-	100	-	120	-	ns
		V _{CC} = 4.5 V	16	6	-	20	-	24	-	ns
		V _{CC} = 6.0 V	14	5	-	17	-	20	-	ns
		MR (HIGH); see Figure 10								
		V _{CC} = 2.0 V	80	25	-	100	-	120	-	ns
		V _{CC} = 4.5 V	16	9	-	20	-	24	-	ns
		V _{CC} = 6.0 V	14	7	-	17	-	20	-	ns
t _{rec}	recovery time	MR to RS; see Figure 10								
		V _{CC} = 2.0 V	100	28	-	125	-	150	-	ns
		V _{CC} = 4.5 V	20	10	-	25	-	30	-	ns
		V _{CC} = 6.0 V	17	8	-	21	-	26	-	ns

Table 6. Dynamic characteristics ...continuedGND = 0 V; $C_L = 50$ pF unless otherwise specified; for test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
$f_{\max}$	maximum frequency	RS; see Figure 8								
		$V_{CC} = 2.0$ V	6	26	-	4.8	-	4	-	MHz
		$V_{CC} = 4.5$ V	30	80	-	24	-	20	-	MHz
		$V_{CC} = 5.0$ V; $C_L = 15$ pF	-	87	-	-	-	-	-	MHz
		$V_{CC} = 6.0$ V	35	95	-	28	-	24	-	MHz
C_{PD}	power dissipation capacitance	$V_I = \text{GND to } V_{CC}$; $V_{CC} = 5$ V; $f_i = 1$ MHz	[4]	-	40	-	-	-	-	pF
74HCT4060-Q100										
t_{pd}	propagation delay	RS to Q3; see Figure 8								
		$V_{CC} = 4.5$ V	-	33	66	-	83	-	99	ns
		$V_{CC} = 5.0$ V; $C_L = 15$ pF	-	31	-	-	-	-	-	ns
		Qn to Qn+1; see Figure 9								
		$V_{CC} = 4.5$ V	-	8	16	-	20	-	24	ns
		$V_{CC} = 5.0$ V; $C_L = 15$ pF	-	6	-	-	-	-	-	ns
t_{PHL}	HIGH to LOW propagation delay	MR to Qn; see Figure 10								
		$V_{CC} = 4.5$ V	-	21	44	-	55	-	66	ns
		$V_{CC} = 5.0$ V; $C_L = 15$ pF	-	18	-	-	-	-	-	ns
t_t	transition time	Qn; see Figure 8								
		$V_{CC} = 4.5$ V	-	7	15	-	19	-	22	ns
t_w	pulse width	RS (HIGH or LOW); see Figure 8								
		$V_{CC} = 4.5$ V	16	6	-	20	-	24	-	ns
		MR (HIGH); see Figure 10								
		$V_{CC} = 4.5$ V	16	6	-	20	-	24	-	ns
t_{rec}	recovery time	MR to RS; see Figure 10								
		$V_{CC} = 4.5$ V	26	13	-	33	-	39	-	ns
$f_{\max}$	maximum frequency	RS; see Figure 8								
		$V_{CC} = 4.5$ V	30	80	-	24	-	20	-	MHz
		$V_{CC} = 5.0$ V; $C_L = 15$ pF	-	88	-	-	-	-	-	MHz

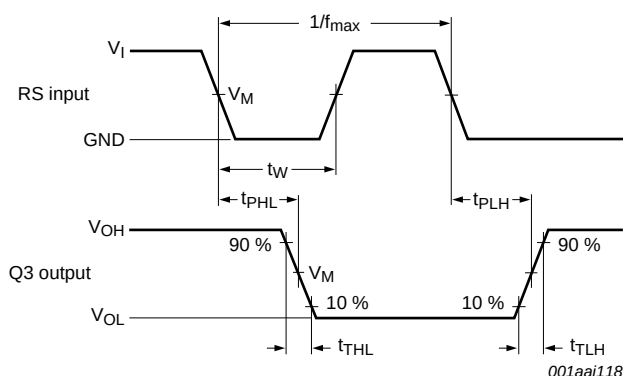
Table 6. Dynamic characteristics ...continued

$GND = 0\text{ V}$; $C_L = 50\text{ pF}$ unless otherwise specified; for test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC} – 1.5 V; V _{CC} = 5 V; f _i = 1 MHz	[4] -	40	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [2] Q_{n+1} is the next Q_n output.
- [3] t_i is the same as t_{THL} and t_{TLH} .
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):
$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$$
 where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



Measurement points are given in [Table 7](#).

V_{OI} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 8. Waveforms showing the clock (RS) to output (Q3) propagation delays, the clock pulse width, the output transition times and the maximum clock frequency

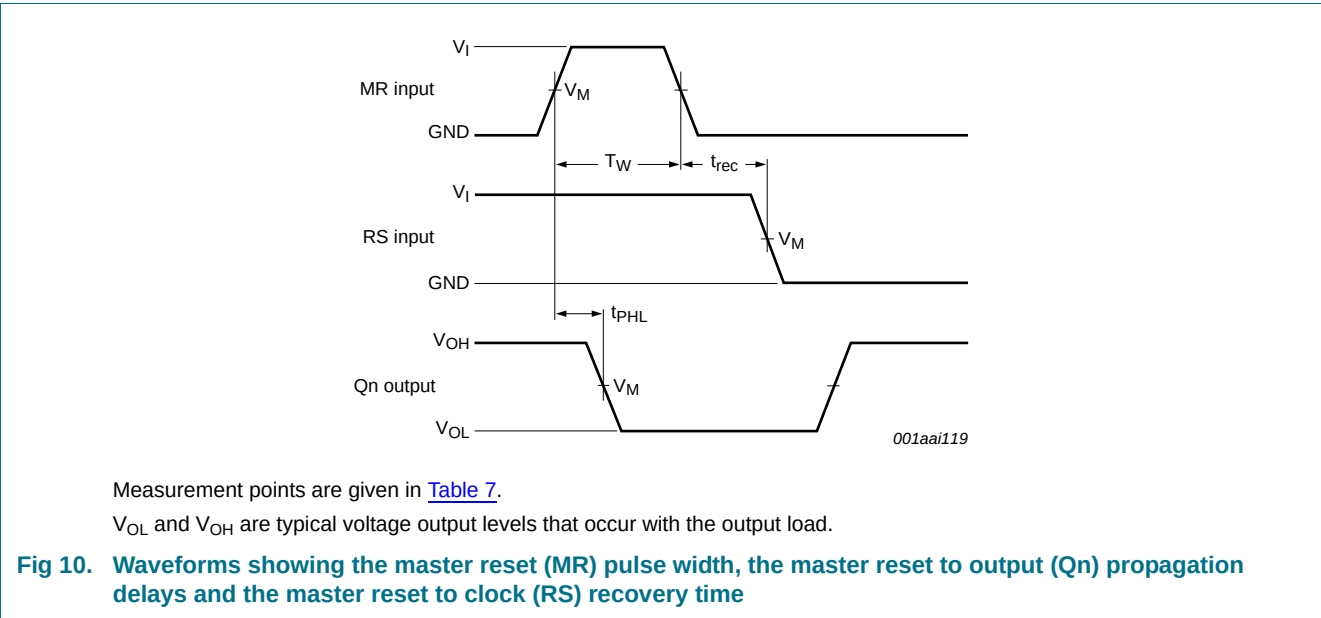
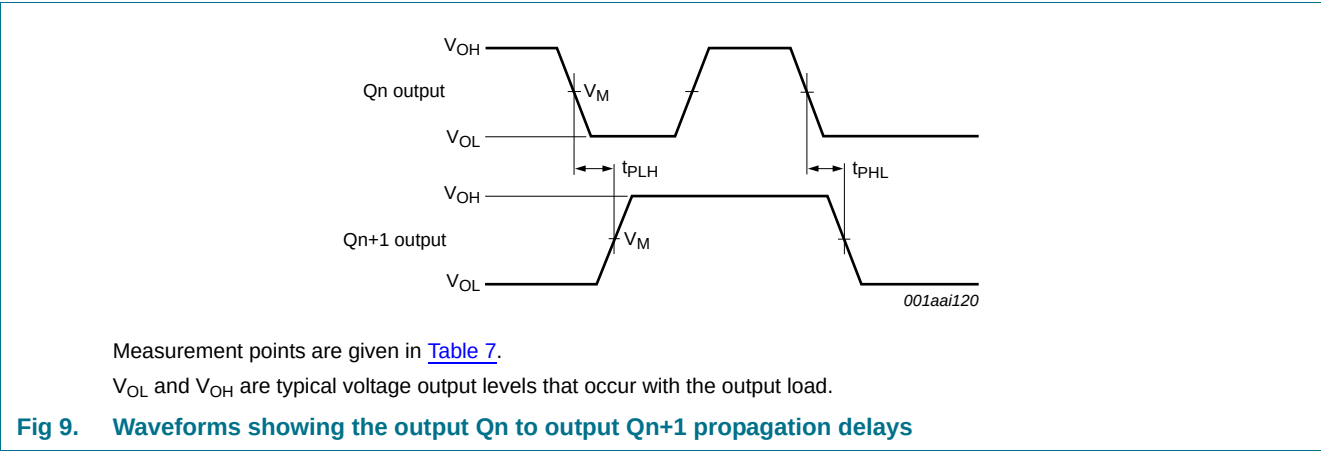
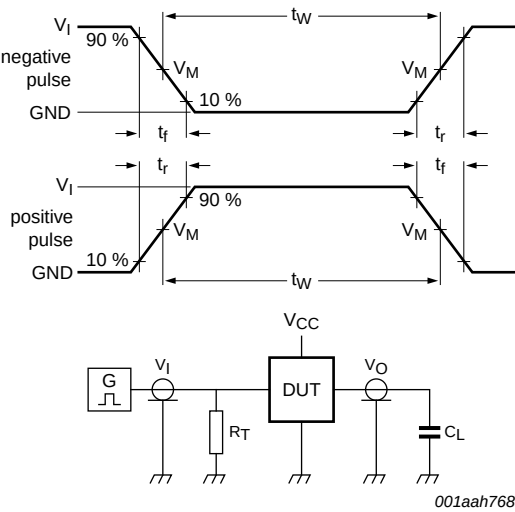


Table 7. Measurement points

Type	Input	Output
	V_M	V_M
74HC4060-Q100	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74HCT4060-Q100	1.3 V	1.3 V



Test data is given in [Table 8](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

Fig 11. Test circuit for measuring switching times

Table 8. Test data

Type	Input		Load
	V_I	t_r, t_f	C_L
74HC4060-Q100	V_{CC}	6 ns	15 pF, 50 pF
74HCT4060-Q100	3 V	6 ns	15 pF, 50 pF

13. RC oscillator

13.1 Timing component limitations

The oscillator frequency is mainly determined by $R_t C_t$, provided $R_2 \approx 2R_t$ and $R_2 C_2 \ll R_t C_t$. The function of R_2 is to minimize the influence of the forward voltage across the input protection diodes on the frequency. The stray capacitance C_2 should be kept as small as possible. In consideration of accuracy, C_t must be larger than the inherent stray capacitance. R_t must be larger than the ON resistance in series with it, which typically is 280 Ω at $V_{CC} = 2.0$ V, 130 Ω at $V_{CC} = 4.5$ V and 100 Ω at $V_{CC} = 6.0$ V.

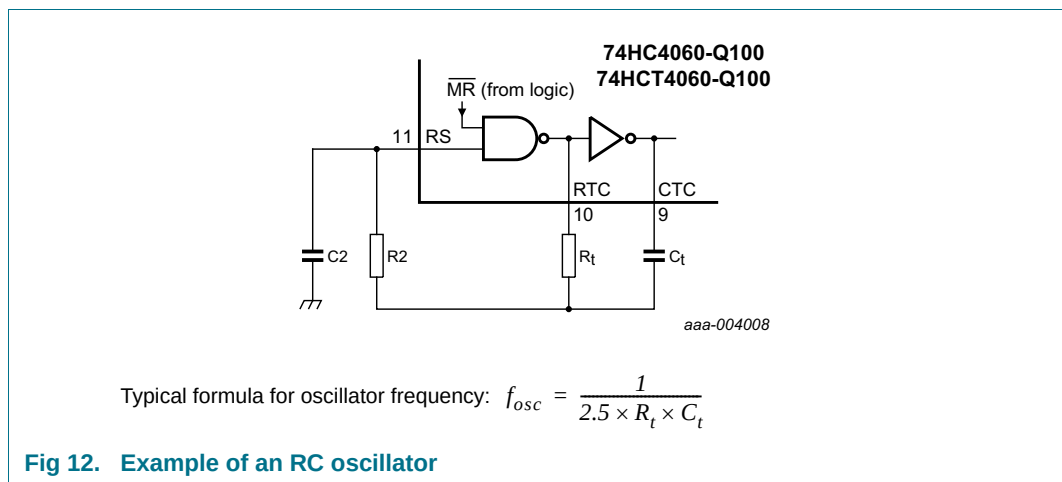


Fig 12. Example of an RC oscillator

The recommended values for these components to maintain agreement with the typical oscillation formula are:

$C_t > 50$ pF, up to any practical value and $10 \text{ k}\Omega < R_t < 1 \text{ M}\Omega$.

In order to avoid start-up problems, $R_t \geq 1 \text{ k}\Omega$.

13.2 Typical crystal oscillator circuit

In [Figure 13](#), R_2 is the power limiting resistor. For starting and maintaining oscillation, a minimum transconductance is necessary, so R_2 must not be too large. A practical value for R_2 is 2.2 k Ω .

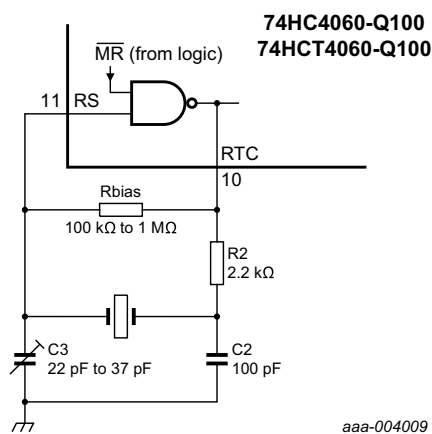
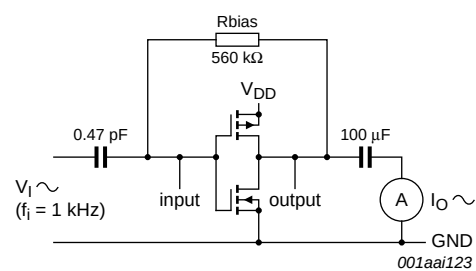
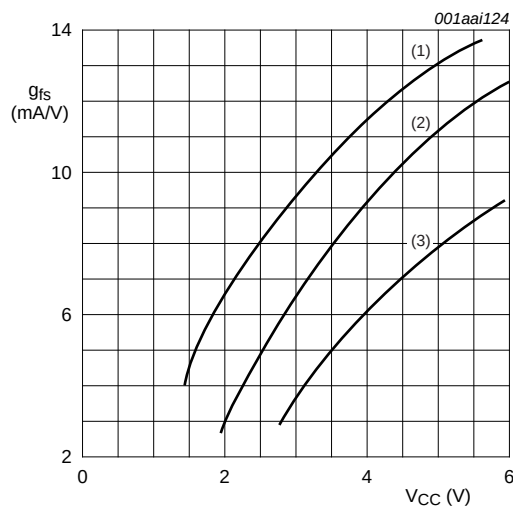


Fig 13. External component connection for a crystal oscillator



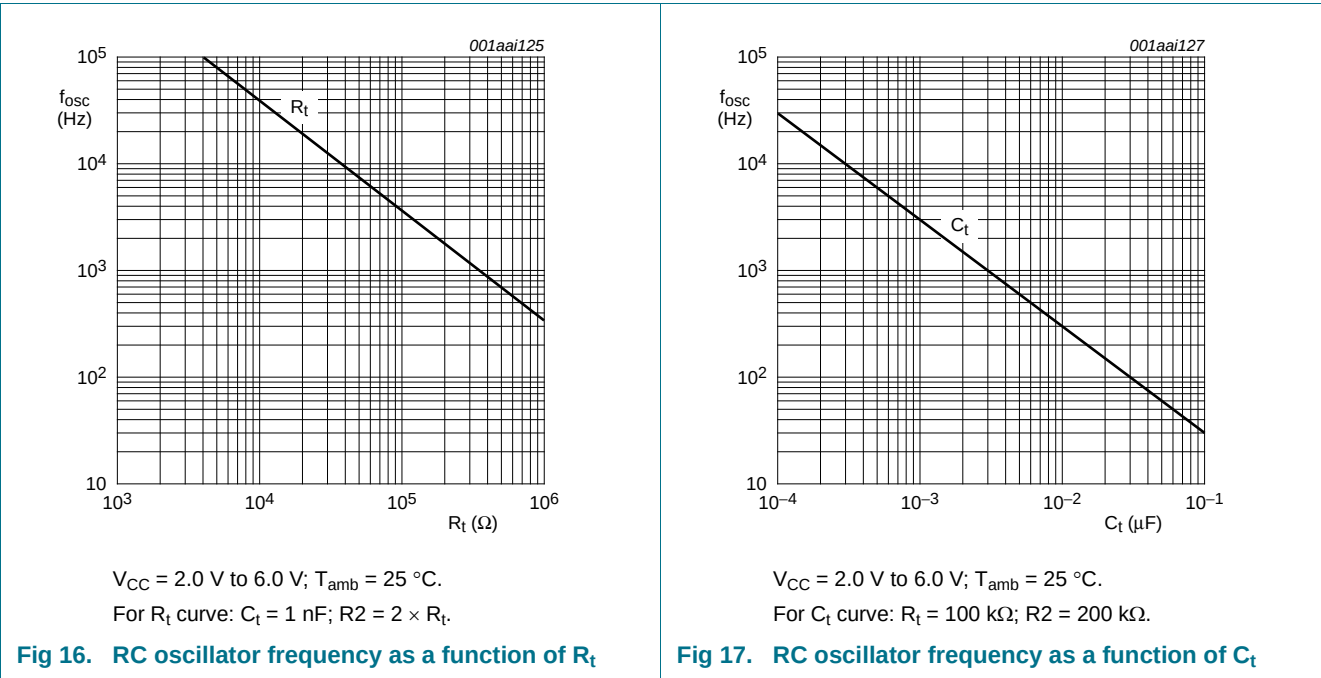
$g_{fs} = \Delta I_O / \Delta V_I$ at V_O is constant; MR = LOW.
See also [Figure 15](#).

Fig 14. Test set-up for measuring forward transconductance



T_{amb} = 25 °C.
(1) Maximum.
(2) Typical.
(3) Minimum.

Fig 15. Typical forward transconductance as function of the supply voltage



14. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

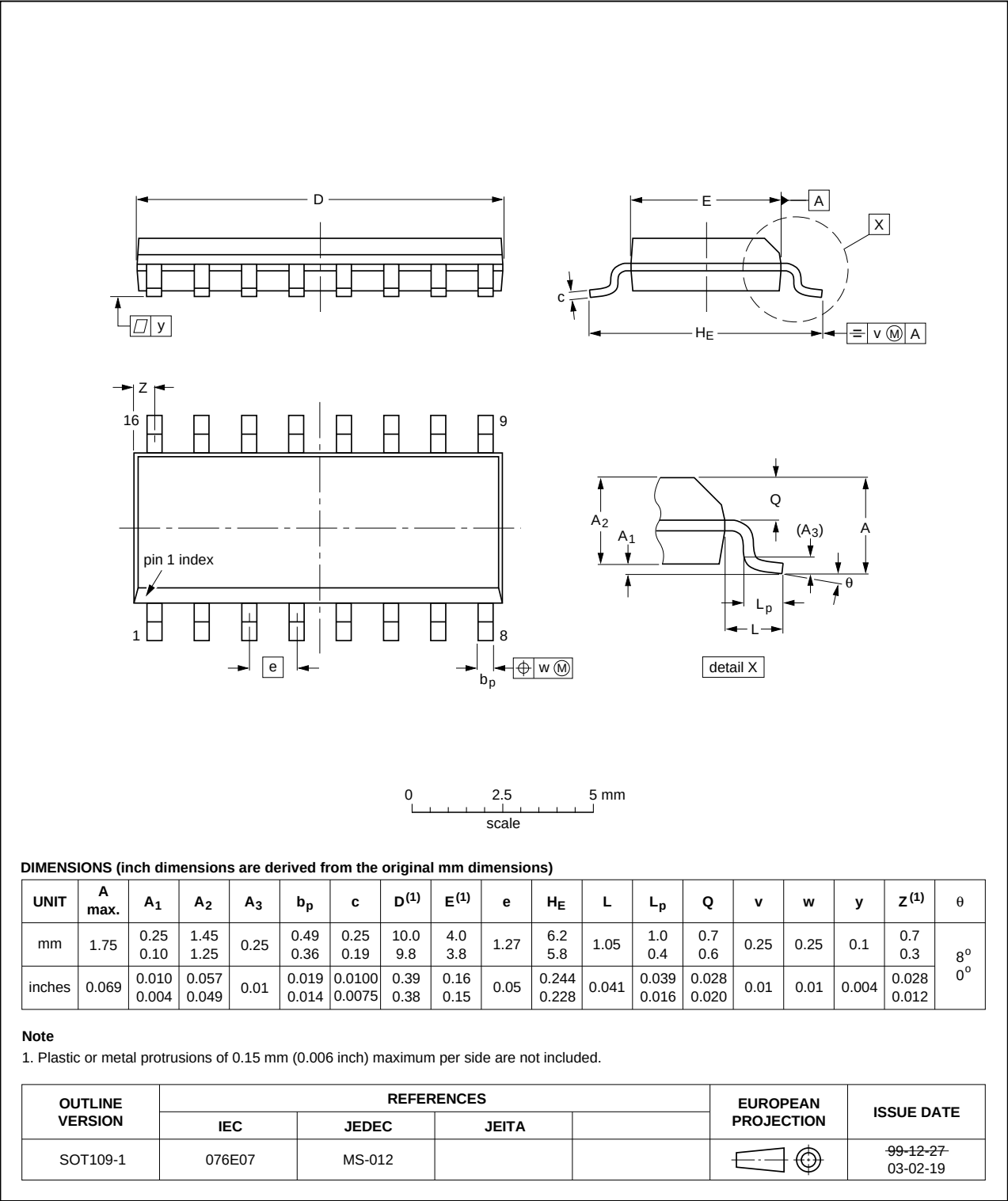


Fig 18. Package outline SOT109-1 (SO16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

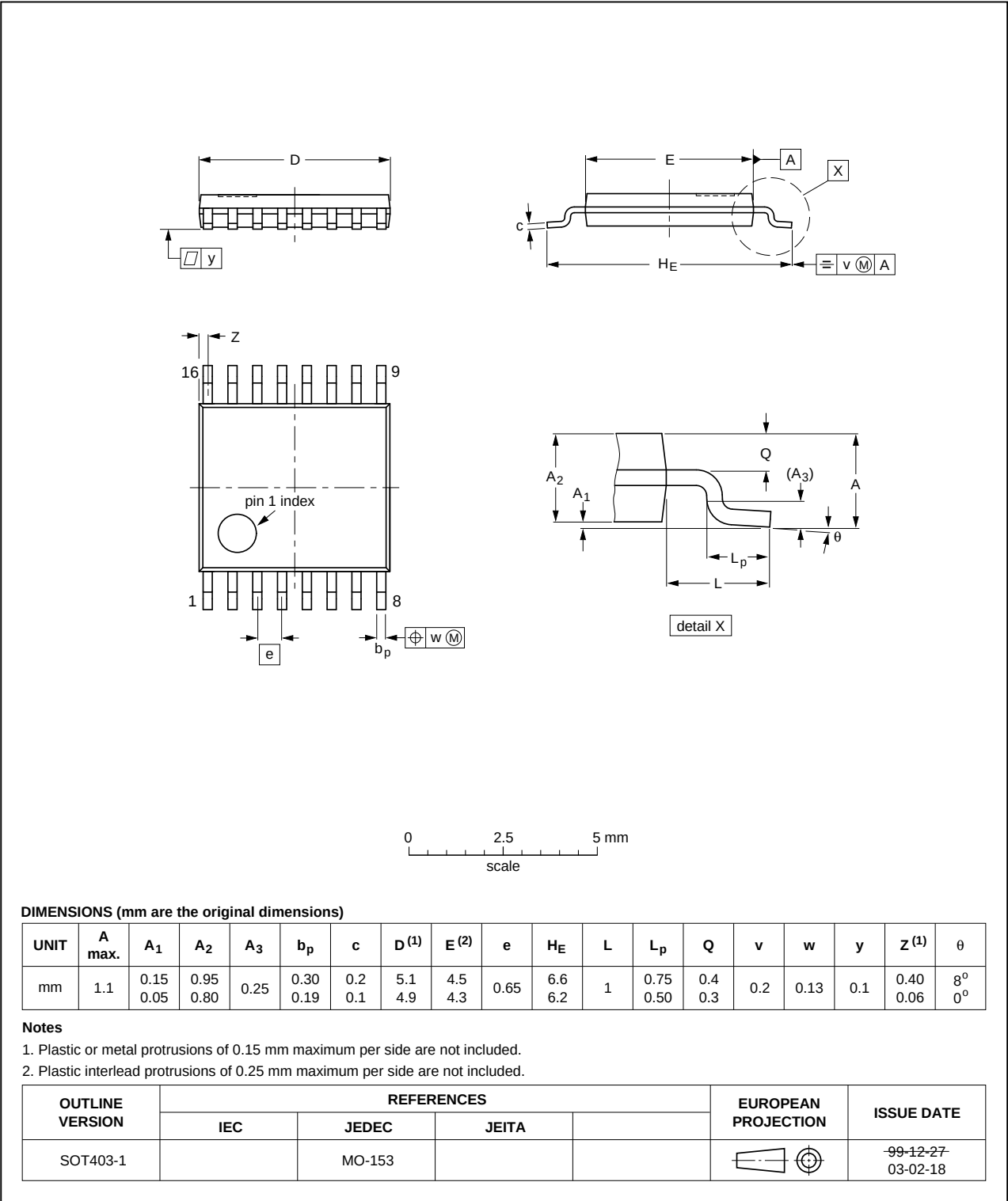


Fig 19. Package outline SOT403-1 (TSSOP16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;
16 terminals; body 2.5 x 3.5 x 0.85 mm

SOT763-1

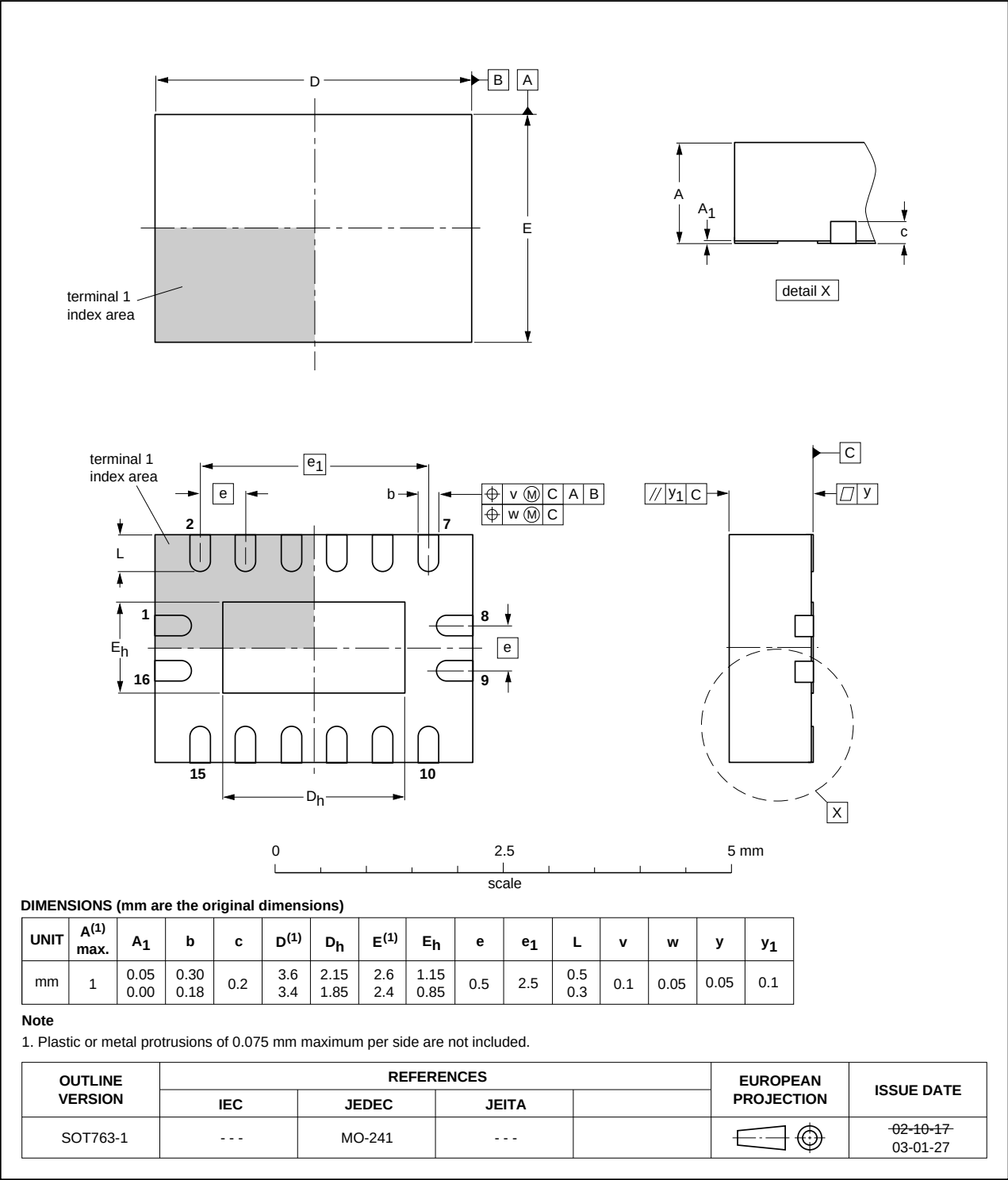


Fig 20. Package outline SOT763-1 (DHVQFN16)

15. Abbreviations

Table 9. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

16. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT4060_Q100 v.1	20120802	Product data sheet	-	-

17. Legal information

17.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

17.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

17.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This NXP Semiconductors product has been qualified for use in automotive applications. Unless otherwise agreed in writing, the product is not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

17.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

18. Contact information

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

19. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Ordering information	2
5	Functional diagram	2
6	Pinning information	4
6.1	Pinning	4
6.2	Pin description	4
7	Functional description	5
8	Limiting values	5
9	Recommended operating conditions	6
10	Static characteristics	6
11	Dynamic characteristics	10
12	Waveforms	12
13	RC oscillator	15
13.1	Timing component limitations	15
13.2	Typical crystal oscillator circuit	15
14	Package outline	18
15	Abbreviations	21
16	Revision history	21
17	Legal information	22
17.1	Data sheet status	22
17.2	Definitions	22
17.3	Disclaimers	22
17.4	Trademarks	23
18	Contact information	23
19	Contents	24

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2012.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 2 August 2012

Document identifier: 74HC_HCT4060_Q100

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9